

What is claimed as new and desired to be protected by Letters Patent of the United States is:

1. A plating method comprising:
providing on a wafer a die with a contact having a first surface area;
providing a supplemental plating structure on said wafer, said supplemental plating structure having a surface area larger than said first surface area;
conductively connecting said supplemental plating structure to said contact; and
plating said supplemental plating structure and said contact.
2. The method of claim 1, further comprising discarding said supplemental plating structure after said plating step.
3. The method of claim 1, further comprising testing said die using said supplemental plating structure as a probe.
4. The method of claim 1, wherein said supplemental plating structure is located in a street area of said wafer.
5. The method of claim 1, wherein said conductive connection is located at least in part in a street area of said wafer.
6. The method of claim 1, further comprising disconnecting said conductive connection after said plating operation.
7. The method of claim 1, wherein said supplemental plating structure is located on said wafer outside an area where dice are formed on said wafer.
8. The method of claim 1, wherein said supplemental plating structure is a sacrificial area which is located at least partly over said die.

9. The method of claim 1, wherein said conductive connection is located at least partly over said die.

10. The method of claim 1, wherein said plating occurs in an electroless bath.

11. The method of claim 10, wherein said electroless bath comprises a nickel salt, a hypophosphite salt, an organic acid or a chelating agent, and a stabilizer.

12. The method of claim 11, wherein said nickel salt is NiSO_4 .

13. The method of claim 11, wherein said hypophosphite salt is NaH_2PO_2 or $\text{NH}_4\text{H}_2\text{PO}_2$.

14. The method of claim 11, wherein said stabilizer is selected from the group consisting of Pb, Cd, and $\text{CH}_4\text{N}_2\text{S}$.

15. A die testing method comprising:

fabricating on a wafer a die with a contact feature having a first surface area;

fabricating on said wafer a supplemental plating structure having a surface area larger than said first surface area;

fabricating a conductive connection between said supplemental plating structure and said contact feature; and

testing said die using said supplemental plating structure as a probe point.

16. The die testing method of claim 15, wherein said step of fabricating comprises plating said contact feature and said supplemental plating structure prior to said step of testing.

17. The die testing method of claim 16, wherein said plating occurs in an electroless bath.

18. The die testing method of claim 17, wherein said electroless bath comprises a nickel salt, a hypophosphite salt, a stabilizer, and an organic acid or a chelating agent.

19. The method of claim 18, wherein said nickel salt is NiSO_4 .

20. The method of claim 18, wherein said hypophosphite salt is NaH_2PO_2 or $\text{NH}_4\text{H}_2\text{PO}_2$.

21. The method of claim 18, wherein said stabilizer is selected from the group consisting of Pb, Cd, and $\text{CH}_4\text{N}_2\text{S}$.

22. An integrated circuit wafer, comprising:
a plurality of dice, each of said dice having at least one first platable feature; and
at least one second platable feature conductively connected to said at least one first platable feature, said second platable feature having a larger surface area than said first platable feature.

23. The wafer of claim 22, wherein said second platable feature assists in plating said first platable feature.

24. The wafer of claim 23, wherein said second platable feature also functions as a probe point for testing said dice.

25. The wafer of claim 22, wherein said second platable feature is connected to said plurality of dice.

26. The wafer of claim 22, wherein said second platable feature is a sacrificial platable feature.

27. The wafer of claim 22, wherein the platable features are electroless-plated features.

28. The wafer of claim 27, wherein the electroless-plated features are plated in a bath that comprises a nickel salt, a hypophosphite salt, a stabilizer, and an organic acid or a chelating agent.

29. A plating method comprising:
providing a plating bath comprising:

- a nickel salt;
- a hypophosphite salt;
- at least one organic acid or chelating agent; and
- a stabilizer;

immersing in said plating bath a wafer, said wafer containing a plurality of dies each having contacts, and supplemental plating structures, said contacts and said supplemental plating structures being conductively connected; and
plating said contacts and said supplemental plating structures.

30. The plating method of claim 29, wherein said stabilizer is selected from the group consisting of Pb, Cd, and $\text{CH}_4\text{N}_2\text{S}$.

31. The plating method of claim 30, wherein said plating bath is an electroless bath.

32. The plating method of claim 31, wherein said nickel salt is NiSO_4 .

33. The plating method of claim 32, wherein said hypophosphite salt is NaH_2PO_2 or $\text{NH}_4\text{H}_2\text{PO}_2$.

34. The plating method of claim 33, wherein said supplemental plating structures are sacrificial.

35. The plating method of claim 29, wherein said conductive connections are sacrificial.

36. The plating method of claim 29, wherein at least one conductive connection is routed over at least one die.